

Platon A Karaseov

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/8383255/publications.pdf>

Version: 2024-02-01

47
papers

370
citations

840776

11
h-index

888059

17
g-index

51
all docs

51
docs citations

51
times ranked

270
citing authors

#	ARTICLE	IF	CITATIONS
1	Radiation tolerance of GaN: the balance between radiation-stimulated defect annealing and defect stabilization by implanted atoms. Journal Physics D: Applied Physics, 2022, 55, 175103.	2.8	2
2	Breakdown Strength of Polypropylene Films Demetallized by High-Power Surface Discharge. , 2021, , .		0
3	Formation of wear-resistant graphite/diamond-like carbon nanocomposite coatings on Ti using accelerated C60-ions. Surface and Coatings Technology, 2021, 424, 127670.	4.8	6
4	Formation of Functional Conductive Carbon Coating on Si by C60 Ion Beam. Springer Proceedings in Physics, 2021, , 131-139.	0.2	5
5	Impact of Chemical Effects on Topography and Thickness of Modified GaN Surface Layers Bombarded by F and Ne Ions. Springer Proceedings in Physics, 2021, , 151-157.	0.2	0
6	Study of Low Energy Ion Beam-Assisted Mixing in Al/Sb Bilayer. , 2021, , .		0
7	Optical properties of plasmonic metal nanoparticles on GaN surface. Journal of Physics: Conference Series, 2021, 2086, 012127.	0.4	1
8	The formation of radiation damage in GaN during successive bombardment by light ions of various energies. Vacuum, 2020, 173, 109149.	3.5	5
9	Formation of Au Nanoparticles and Features of Etching of a Si Substrate under Irradiation with Atomic and Molecular Ions. Semiconductors, 2020, 54, 137-143.	0.5	5
10	Electrooptical Properties of TiO ₂ Doped with Gold Nanoparticles. Semiconductors, 2020, 54, 1885-1888.	0.5	5
11	Substrate modification influence on properties of nanocomposite based on TiO ₂ and gold nanoparticles. Journal of Physics: Conference Series, 2019, 1236, 012025.	0.4	4
12	International Conference "Emerging Trends in Applied and Computational Physics 2019" (ETACP-2019). Journal of Physics: Conference Series, 2019, 1236, 011001.	0.4	0
13	Do Chemical Effects Affect the Accumulation of Structural Damage during the Implantation of Fluorine Ions into GaN?. Semiconductors, 2019, 53, 1415-1418.	0.5	7
14	Effect of monatomic and molecular ion irradiation on time resolved photoluminescence decay in GaN. Nuclear Instruments & Methods in Physics Research B, 2019, 458, 164-168.	1.4	4
15	Formation of Radiation Defects by Proton Braking in Lightly Doped n- and p-SiC Layers. Semiconductors, 2018, 52, 310-315.	0.5	3
16	In-situ transport and microstructural evolution in GaN Schottky diodes and epilayers exposed to swift heavy ion irradiation. Journal of Applied Physics, 2018, 123, 161539.	2.5	14
17	The mechanism of charge carrier generation at the TiO ₂ /n-Si heterojunction activated by gold nanoparticles. Semiconductor Science and Technology, 2018, 33, 075014.	2.0	12
18	Dislocation-related photoluminescence in silicon implanted with fluorine ions. Technical Physics Letters, 2017, 43, 50-52.	0.7	5

#	ARTICLE	IF	CITATIONS
19	Ranges of 10–350 keV H and H ₂ ions in (1 1 1) diamond. Nuclear Instruments & Methods in Physics Research B, 2017, 406, 634-637.	1.4	2
20	Single and molecular ion irradiation-induced effects in GaN: experiment and cumulative MD simulations. Journal Physics D: Applied Physics, 2017, 50, 505110.	2.8	4
21	The effect of diborane additive on the plasma-chemical properties of deposited carbon films. Technical Physics Letters, 2017, 43, 81-84.	0.7	5
22	Experimental study and MD simulation of damage formation in GaN under atomic and molecular ion irradiation. Vacuum, 2016, 129, 166-169.	3.5	8
23	Swift heavy ion irradiation of metal containing tetrahedral amorphous carbon films. Nuclear Instruments & Methods in Physics Research B, 2016, 379, 162-166.	1.4	4
24	Effect of an increase in the density of collision cascades on the efficiency of the generation of primary displacements during the ion bombardment of Si. Semiconductors, 2016, 50, 989-995.	0.5	7
25	Modification of properties of metal containing carbon films by swift heavy ion irradiation. , 2014, , .		1
26	Effect of ion bombardment on the phase composition and mechanical properties of diamond-like carbon films. Journal of Surface Investigation, 2014, 8, 45-49.	0.5	12
27	Effect of growth conditions on carbon film properties. , 2014, , .		0
28	Nonlinear optical effect upon the irradiation of GaN with cluster ions. Semiconductors, 2014, 48, 446-450.	0.5	8
29	Defect clustering in irradiation of GaN by single and molecular ions. Vacuum, 2014, 105, 88-90.	3.5	11
30	Damage formation in Si under irradiation with PF _n ⁺ ions of different energies. Semiconductors, 2013, 47, 242-246.	0.5	12
31	Effect of collision cascade density on swelling and surface topography of GaN. Nuclear Instruments & Methods in Physics Research B, 2013, 315, 257-260.	1.4	3
32	Effects of defect clustering on optical properties of GaN by single and molecular ion irradiation. Journal of Applied Physics, 2013, 114, .	2.5	9
33	Atomistic simulation of damage production by atomic and molecular ion irradiation in GaN. Journal of Applied Physics, 2012, 112, .	2.5	18
34	Molecular effect on surface topography of GaN bombarded with PF ₄ ions. Vacuum, 2012, 86, 1638-1641.	3.5	9
35	Model for radiation damage buildup in GaN. Nuclear Instruments & Methods in Physics Research B, 2012, 277, 80-83.	1.4	16
36	Residual stress in diamond-like carbon films: Role of growth conditions and ion irradiation. Journal of Surface Investigation, 2010, 4, 241-244.	0.5	9

#	ARTICLE	IF	CITATIONS
37	Influence of ion irradiation on internal residual stress in DLC films. Nuclear Instruments & Methods in Physics Research B, 2010, 268, 3107-3110.	1.4	13
38	Structural damage in ZnO bombarded by heavy ions. Vacuum, 2010, 84, 1058-1061.	3.5	22
39	Effect of collision cascade density on radiation damage in SiC. Nuclear Instruments & Methods in Physics Research B, 2009, 267, 1247-1250.	1.4	10
40	Effects of the density of collision cascades: Separating contributions from dynamic annealing and energy spikes. Nuclear Instruments & Methods in Physics Research B, 2009, 267, 2701-2704.	1.4	8
41	Energy spike effects in ion-bombarded GaN. Journal Physics D: Applied Physics, 2009, 42, 085309.	2.8	29
42	Influence of ion bombardment on residual stresses in diamond-like carbon films. Journal of Surface Investigation, 2009, 3, 235-238.	0.5	2
43	Density of displacement cascades for cluster ions: An algorithm of calculation and the influence on damage formation in ZnO and GaN. Semiconductors, 2009, 43, 691-700.	0.5	18
44	Effect of the density of collision cascades on ion implantation damage in ZnO. Journal of Applied Physics, 2007, 102, 083547.	2.5	37
45	Furthering the understanding of ion-irradiation-induced electrical isolation in wide band-gap semiconductors. Nuclear Instruments & Methods in Physics Research B, 2006, 243, 79-82.	1.4	4
46	A model of electrical isolation in GaN and ZnO bombarded with light ions. Semiconductors, 2004, 38, 1179-1186.	0.5	10
47	Computer simulation of electron diffraction by soft crystal potential. , 1998, 3345, 118.		0